Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2842

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & : R_{DS}\ (ON) = 0.4\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & : |Y_{fs}| = 9.0\ S\ (typ.) \\ \bullet & Low\ leakage\ current & : I_{DSS} = 100\ \mu A\ (max)\ (V_{DS} = 500\ V) \\ \bullet & Enhancement-mode & : V_{th} = 2.0 \sim 4.0\ V\ (V_{DS} = 10\ V,\ I_{D} = 1\ mA) \\ \end{array}$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	500	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	500	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	12	Α	
	Pulse (Note 1)	I _{DP}	48	Α	
Drain power dissipatio	n (Tc = 25°C)	P_{D}	40	W	
Single pulse avalanche energy (Note 2)		E _{AS}	364	mJ	
Avalanche current		I _{AR}	12	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	4.0	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

2-10R1B

Weight: 1.9 g (typ.)

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Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 4.3 mH, R_G = 25 Ω , I_{AR} = 12 A

Note 3: Repetitive rating; Pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device.

Please handle with caution.



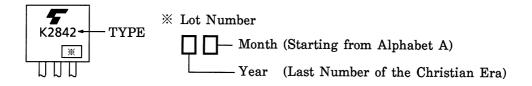
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bro	eakdown voltage	V (BR) GSS	$I_{G} = \pm 10 \mu A, V_{DS} = 0 V$	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source br voltage	reakdown	V _(BR) DSS	I _D = 10 mA, V _{GS} = 0 V	500	_	_	V
Gate threshold v	/oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 6 A	_	0.4	0.52	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 6 A	4.0	9.0	_	S
Input capacitance		C _{iss}		_	2040	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	200	_	pF
Output capacitance		Coss			640	_	
Switching time	Rise time	t _r	V _{GS} _{0V}	_	22	_	- ns
	Turn-on time	t _{on}		_	58	_	
	Fall time	t _f		_	36	_	
	Turn-off time	t _{off}	V_{DD} \rightleftharpoons 200V \rightleftharpoons 20 μ s	_	180	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	45	_	
Gate-source charge		Q _{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$		25	_	nC
Gate-drain ("miller") Charge		Q _{gd}			20	_	

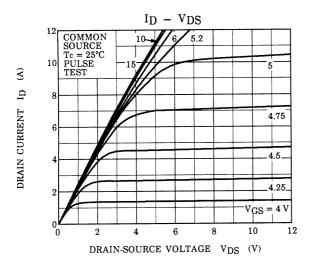
Source-Drain Ratings and Characteristics (Ta = 25°C)

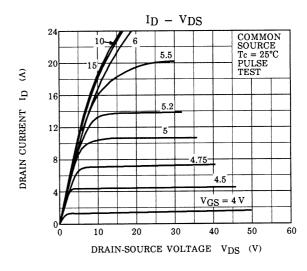
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	12	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	48	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 12 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 12 A, V _{GS} = 0 V dI _{DR} / dt = 100 A / μs		1200		ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 A / μs	_	16	_	μC

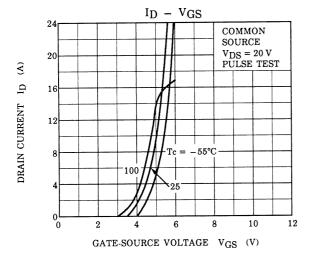
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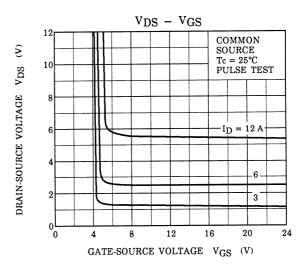


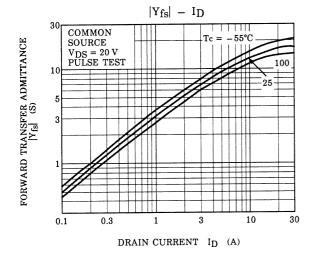
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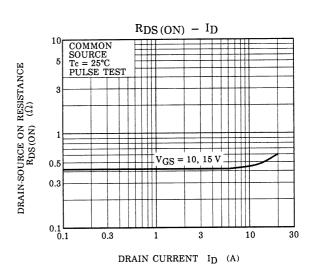




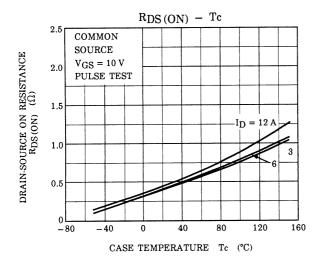


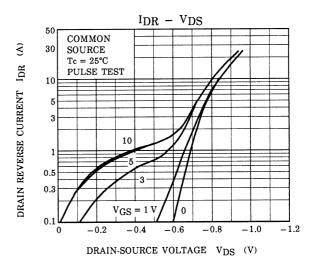


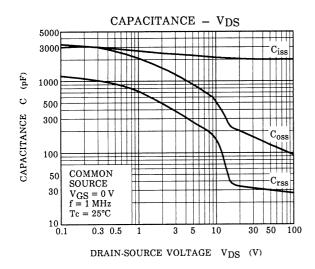


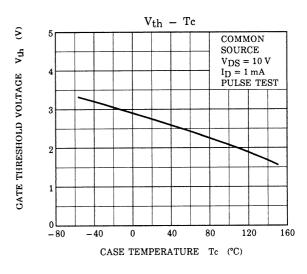


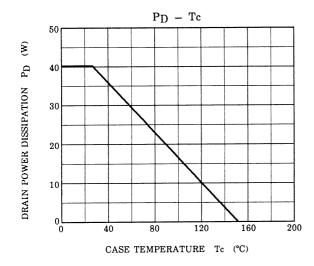
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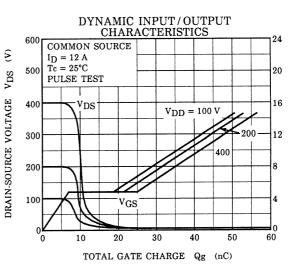






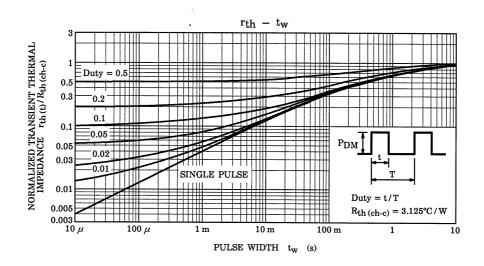


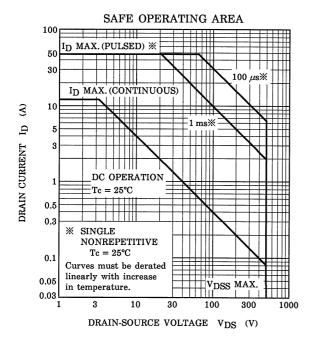


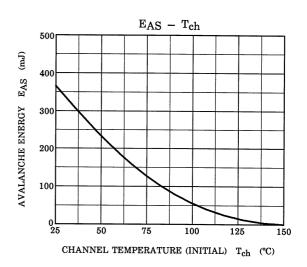


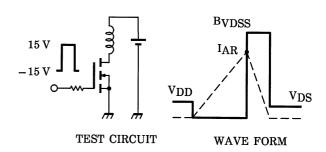
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 VGS









$$\begin{aligned} R_G &= 25~\Omega \\ V_{DD} &= 90~V,~L = 4.3~mH \end{aligned} \qquad E_{AS} &= \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right) \end{aligned}$$

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